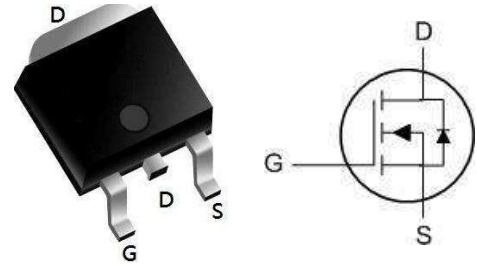


| | | |
|--------------|---------------------------|----------------------|
| BVDSS | R_{DS(on)} | I_D |
| 30V | 6.5mΩ | 60A |



TO252

Absolute Maximum Ratings

| Symbol | Parameter | Rating | | Units |
|---------------------------------------|--|------------|--------------|-------|
| | | 10s | Steady State | |
| V _{DS} | Drain-Source Voltage | 30 | | V |
| V _{GS} | Gate-Source Voltage | ±20 | | V |
| I _D @T _C =25°C | Continuous Drain Current, V _{GS} @ 10V ¹ | 60 | | A |
| I _b @T _C =100°C | Continuous Drain Current, V _{GS} @ 10V ¹ | 33 | | A |
| I _{DM} | Pulsed Drain Current ² | 198 | | A |
| EAS | Single Pulse Avalanche Energy ³ | 36 | | mJ |
| I _{AS} | Avalanche Current | 53.8 | | A |
| P _D @T _C =25°C | Total Power Dissipation ⁴ | 32.5 | | W |
| T _{STG} | Storage Temperature Range | -55 to 175 | | °C |
| T _J | Operating Junction Temperature Range | -55 to 175 | | °C |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|------------------|---|------|------|------|
| R _{θJC} | Thermal Resistance Junction-Case ¹ | --- | 3.56 | °C/W |

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|---|--|--|------|------|-----------|------------|
| Off Characteristic | | | | | | |
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=250\mu A$ | 30 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=30V, V_{GS}=0V,$ | - | - | 1.0 | μA |
| I_{GSS} | Gate to Body Leakage Current | $V_{DS}=0V, V_{GS}=\pm 20V$ | - | - | ± 100 | nA |
| On Characteristics | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=250\mu A$ | 1.0 | 1.5 | 2.5 | V |
| $R_{DS(on)}$ | Static Drain-Source on-Resistance note3 | $V_{GS}=10V, I_D=25A$ | - | 6.5 | 7.5 | m Ω |
| | | $V_{GS}=4.5V, I_D=15A$ | - | 10 | 14 | |
| Dynamic Characteristics | | | | | | |
| C_{iss} | Input Capacitance | $V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$ | - | 1140 | - | pF |
| C_{oss} | Output Capacitance | | - | 175 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 151 | - | pF |
| Q_g | Total Gate Charge | $V_{DS}=15V, I_D=25A,$ $V_{GS}=10V$ | - | 13.3 | - | nC |
| Q_{gs} | Gate-Source Charge | | - | 3.1 | - | nC |
| Q_{gd} | Gate-Drain("Miller") Charge | | - | 5 | - | nC |
| Switching Characteristics | | | | | | |
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DS}=15V,$ $I_D=25A, R_{GEN}=3\Omega,$ $V_{GS}=10V$ | - | 15 | - | ns |
| t_r | Turn-on Rise Time | | - | 19 | - | ns |
| $t_{d(off)}$ | Turn-off Delay Time | | - | 35 | - | ns |
| t_f | Turn-off Fall Time | | - | 21 | - | ns |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| I_S | Maximum Continuous Drain to Source Diode Forward Current | | - | - | 50 | A |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 200 | A |
| V_{SD} | Drain to Source Diode Forward Voltage | $V_{GS}=0V, I_S=30A$ | - | - | 1.2 | V |
| t_{rr} | Body Diode Reverse Recovery Time | $I_F=30A, di/dt=100A/\mu s$ | - | 25 | - | ns |
| Q_{rr} | Body Diode Reverse Recovery Charge | | - | 26 | - | nC |

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

 2. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=15V, V_G=10V, R_G=25\Omega, L=0.5mH, I_{AS}=12A$

 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

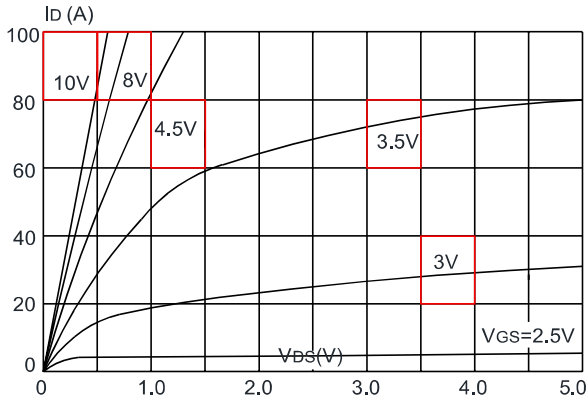


Figure 2: Typical Transfer Characteristics

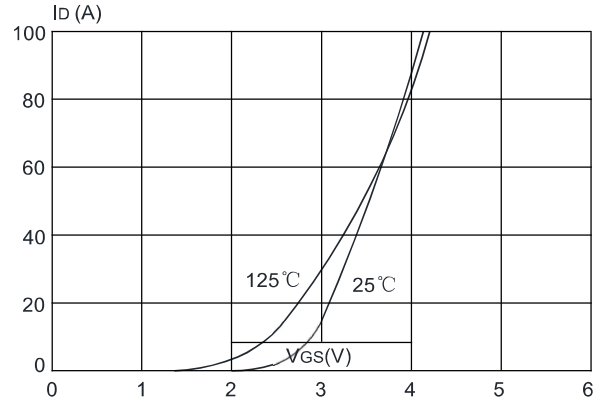


Figure 3: On-resistance vs. Drain Current

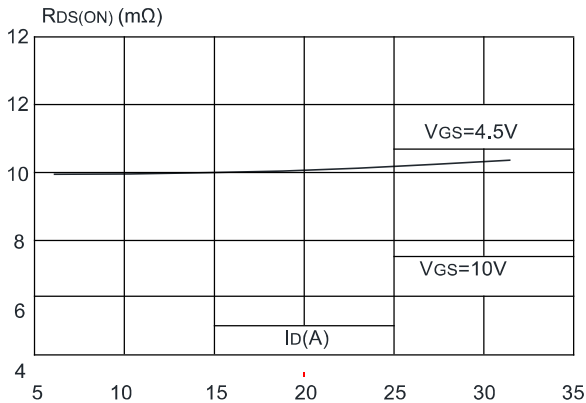


Figure 4: Body Diode Characteristics

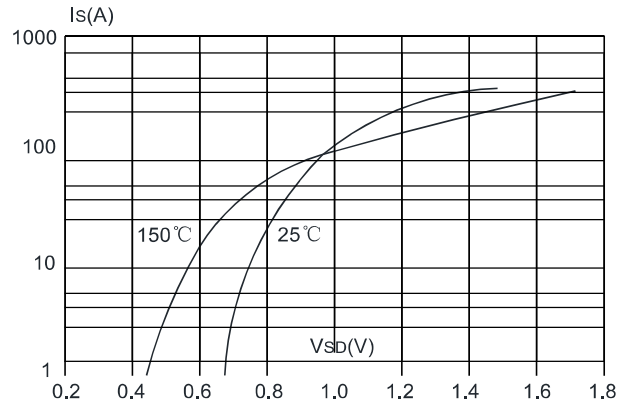


Figure 5: Gate Charge Characteristics

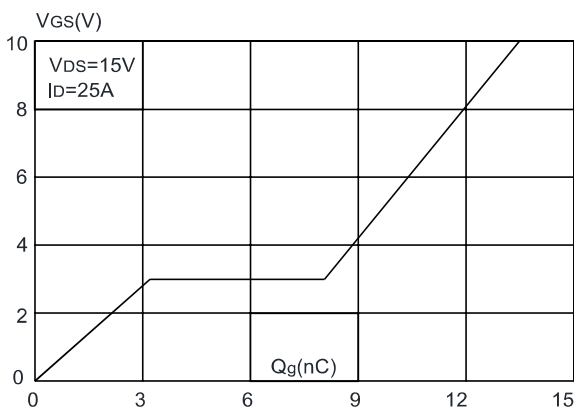


Figure 6: Capacitance Characteristics

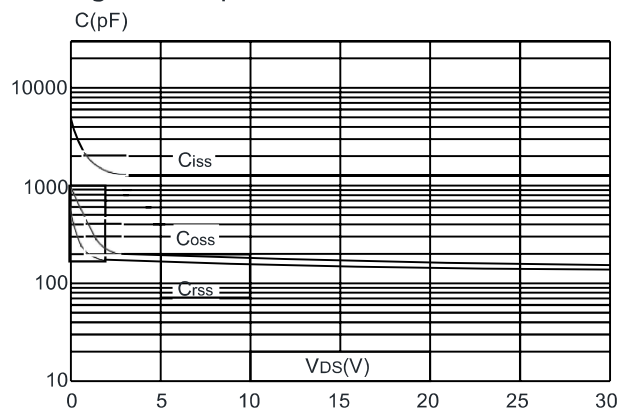


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

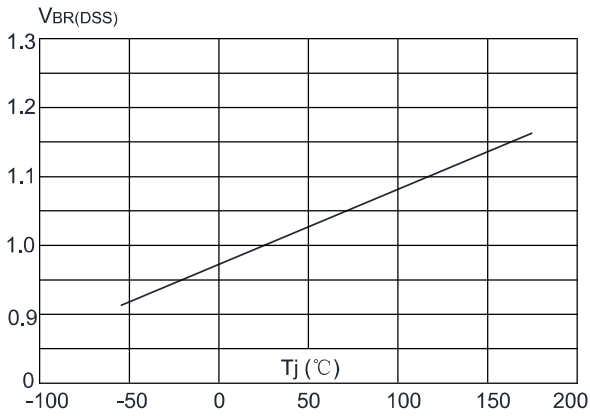


Figure 8: Normalized on Resistance vs. Junction Temperature

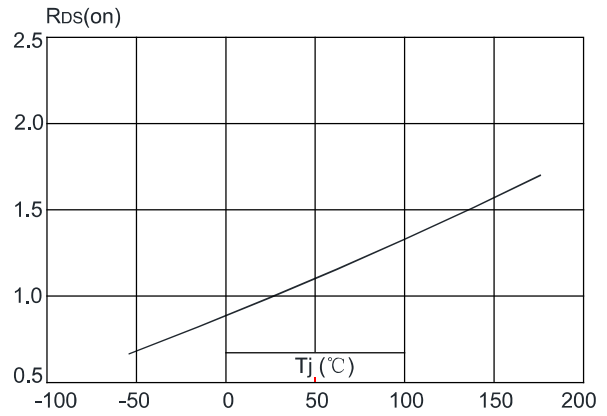
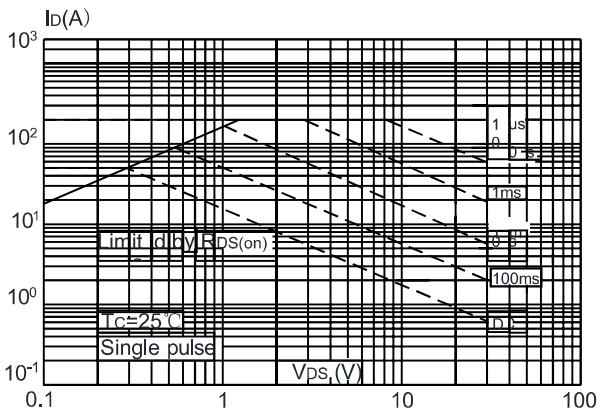


Figure 9: Maximum Safe Operating Area



Maximum Effective Transient Thermal Impedance, Junction-to-Case

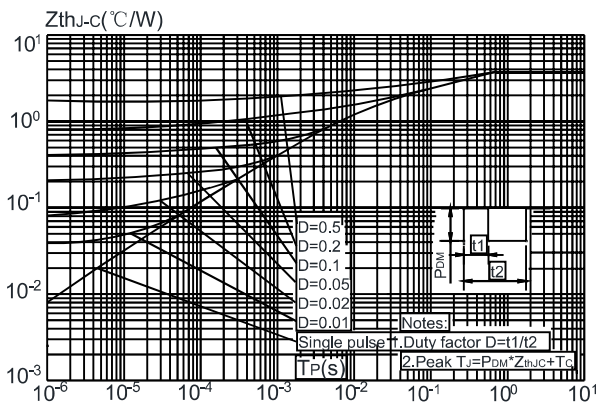
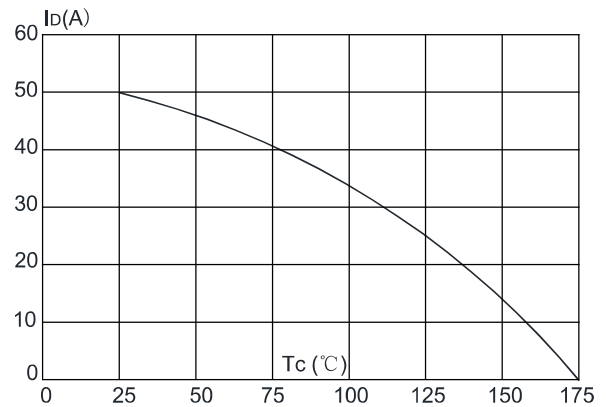


Figure 10: Maximum Continuous Drain Current vs. Case Temperature



Test Circuit

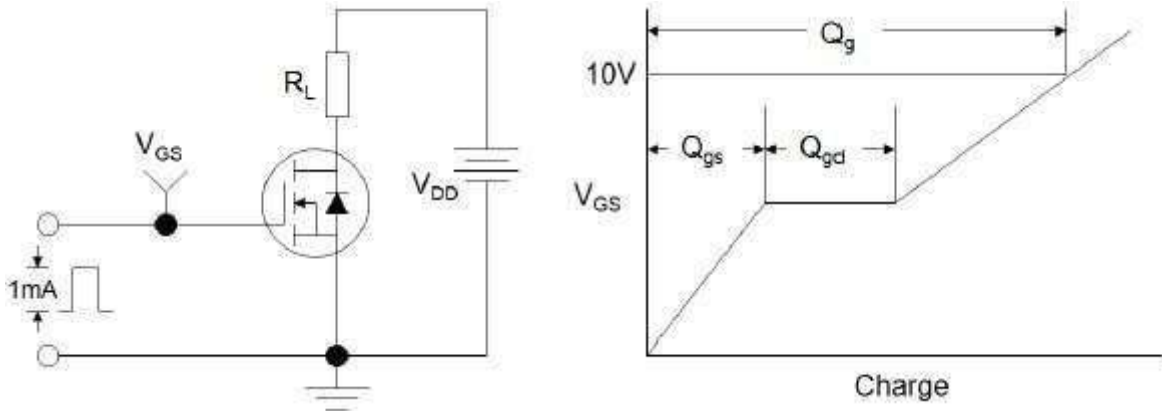


Figure1:Gate Charge Test Circuit & Waveform

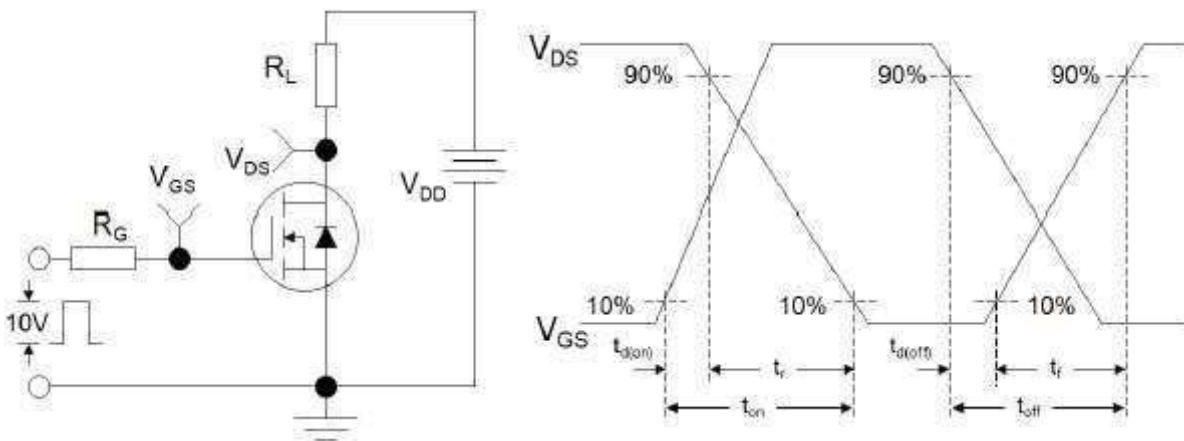


Figure 2: Resistive Switching Test Circuit & Waveforms

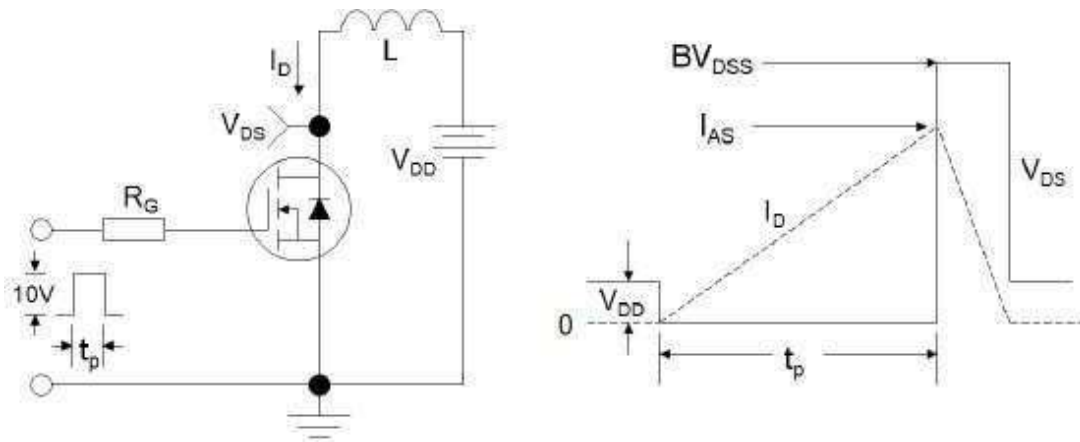
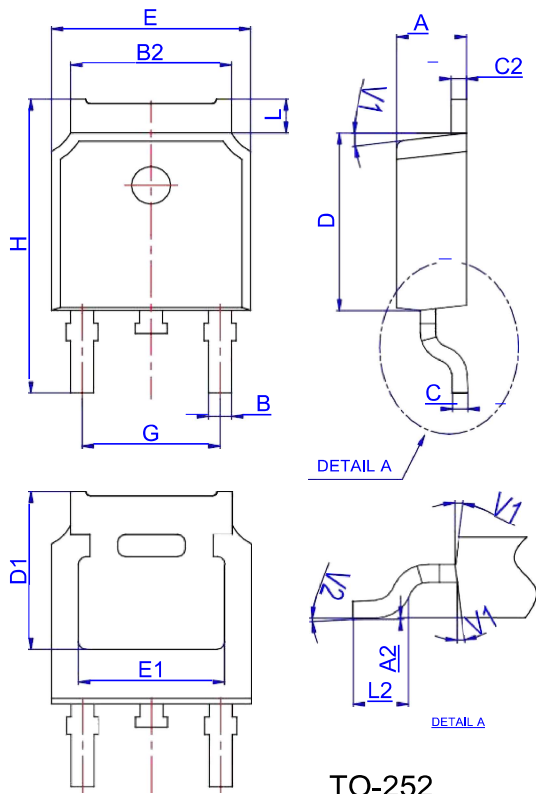


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data TO 252



| Ref. | Dimensions | | | | | |
|------|-------------|------|-------|----------|------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 2.10 | | 2.50 | 0.083 | | 0.098 |
| A2 | 0 | | 0.10 | 0 | | 0.004 |
| B | 0.66 | | 0.86 | 0.026 | | 0.034 |
| B2 | 5.18 | | 5.48 | 0.202 | | 0.216 |
| C | 0.40 | | 0.60 | 0.016 | | 0.024 |
| C2 | 0.44 | | 0.58 | 0.017 | | 0.023 |
| D | 5.90 | | 6.30 | 0.232 | | 0.248 |
| D1 | 5.30REF | | | 0.209REF | | |
| E | 6.40 | | 6.80 | 0.252 | | 0.268 |
| E1 | 4.63 | | | 0.182 | | |
| G | 4.47 | | 4.67 | 0.176 | | 0.184 |
| H | 9.50 | | 10.70 | 0.374 | | 0.421 |
| L | 1.09 | | 1.21 | 0.043 | | 0.048 |
| L2 | 1.35 | | 1.65 | 0.053 | | 0.065 |
| V1 | | 7° | | | 7° | |
| V2 | 0° | | 6° | 0° | | 6° |

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